

Customer No.: 31561  
Application No.: 10/605,793  
Docket No.: 9004-US-PA

### REMARKS

#### Present Status of the Application

Claims 1-14 are pending of which claims 1-3, 5-6, 8-9, 11-12 and 14 have been amended and claims 4, 7, 10 and 13 have been canceled. It is believed that the amendments to claims or specification do not include any new matter nor raise any new issue. Applicant will sequentially address the issues raised by the Examiner as follows:

#### I. The 35 U.S.C. §102 Rejections

Claims 1-14 were rejected under 35 U.S.C. §102(e) as being anticipated by Yamazaki et al, US-2002/0034863, hereinafter YAMAZAKI.

##### 1. YAMAZAKI fails to teach each and every element of the claims.

###### A. Claim 1

It is axiomatic that the cited reference in a §102 rejection must disclose each and every element in the rejected claim. Claim 1 after amendment recites at least the following steps:

forming an optical layer on the amorphous silicon layer;  
forming and patterning a mask layer on the optical layer;  
etching the optical layer to form a heat sink layer and an anti-reflective layer, the heat sink layer being substantially thicker than the anti-reflective layer;

YAMAZAKI fails to disclose or teach at least these steps recited in claim 1.

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Moreover, Applicant would like to point out that the layer with a reference number 102 in Fig. 1A of YAMAZAKI, which the Examiner deems as equivalent to the optical layer of claim 1, is in fact located underneath or below the amorphous silicon layer (104). Accordingly, Applicant respectfully submits that Examiner's interpretation of layer (102) as an optical layer on the amorphous silicon film (104) is due to an error. Therefore, the 35 U.S.C. §102(e) rejection is respectively traversed.

**2. Yamazaki teaches forming an amorphous silicon layer with concave or convex pattern on an insulating film rather than forming an optical layer on the silicon amorphous layer as taught by the present invention.**

Furthermore, YAMASAKI fails to teach, disclose or anticipate a method of inducing lateral differential temperature gradient in the amorphous silicon layer using an optical layer with different thickness and different reflectivity for facilitating/enhancing lateral crystallization. Instead, YAMAZAKI teaches forming an amorphous silicon layer with concave or convex pattern on an insulating film rather than forming an optical layer on the silicon amorphous layer as taught by the present invention.

Based on the foregoing arguments, Applicant respectfully submits that YAMAZAKI fails to teach at least the steps of forming an optical layer on the amorphous silicon layer; and etching the optical layer to form a heat sink layer and an anti-reflective layer, the heat sink layer being substantially thicker than the anti-reflective layer as

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recited in claim 1. Thus, claim 1 is not anticipated by YAMAZAKI and therefore should be allowed.

B. Claim 2, 4-6 and 8

Claims 2, 4-6 and 8 are dependent from claim 1, and therefore should also be allowed for at least their dependency from the allowable base claim 1.

C. Claims 9

Since independent claim 9 also substantially recites the same limitations of claim 1, and therefore should also be allowed for at least the same reasons discussed above with respect to claim 1.

D. Claims 10-14

Claims 10-12 and 14 are dependent from claim 9, and therefore should also be allowed for at least their dependency from the allowable base claim 9.

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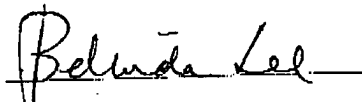
## II. CONCLUSION

In view of the foregoing, it is respectfully submitted that the application is now in condition for allowance. Should the Examiner believe that a telephone interview would help advance the prosecution of this case, the Examiner is requested to contact the undersigned attorney.

Respectfully submitted

Date :

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